74LVT16374A; 74LVTH16374ASheet4U.com

3.3 V 16-bit edge-triggered D-type flip-flop; 3-state

Rev. 07 — 22 March 2010 Produ

Product data sheet

1. **General description**

The 74LVT16374A; 74LVTH16374A are high performance BiCMOS products designed for V_{CC} operation at 3.3 V.

This device is a 16-bit edge-triggered D-type flip-flop featuring non-inverting 3-state outputs. The device can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (nCP), the nQn outputs of the flip-flop take on the logic levels set up at the nDn inputs.

2. Features and benefits

- 16-bit edge-triggered flip-flop
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus-hold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- Power-up reset
- Power-up 3-state
- No bus current loading when output is tied to 5 V bus
- Latch-up protection:
 - ◆ JESD78B Class II exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V

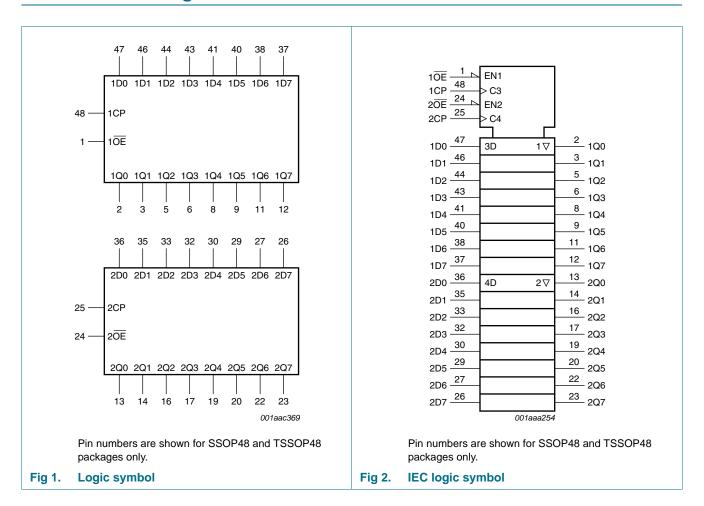


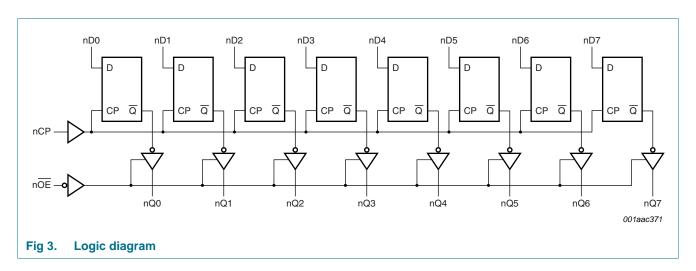
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVT16374ADL	–40 °C to +85 °C	SSOP48	plastic shrink small outline package; 48 leads; body width 7.5 mm	SOT370-1
74LVT16374ADGG	–40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package;	SOT362-1
74LVTH16374ADGG			48 leads; body width 6.1 mm	
74LVT16374AEV	–40 °C to +85 °C	VFBGA56	plastic very thin fine-pitch ball grid array package; 56 balls; body $4.5 \times 7 \times 0.65$ mm	SOT702-1
74LVTH16374ABQ	–40 °C to +85 °C	HXQFN60U	plastic thermal enhanced extremely thin quad flat package; no leads; 60 terminals; UTLP based; body $4\times6\times0.5$ mm	SOT1134-1

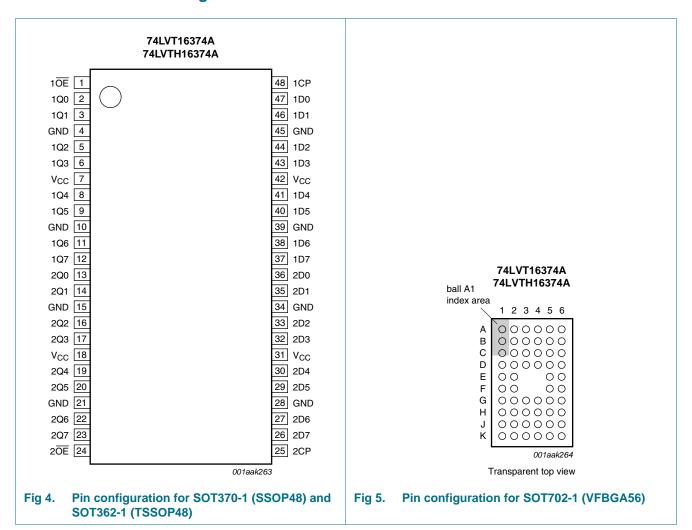
4. Functional diagram

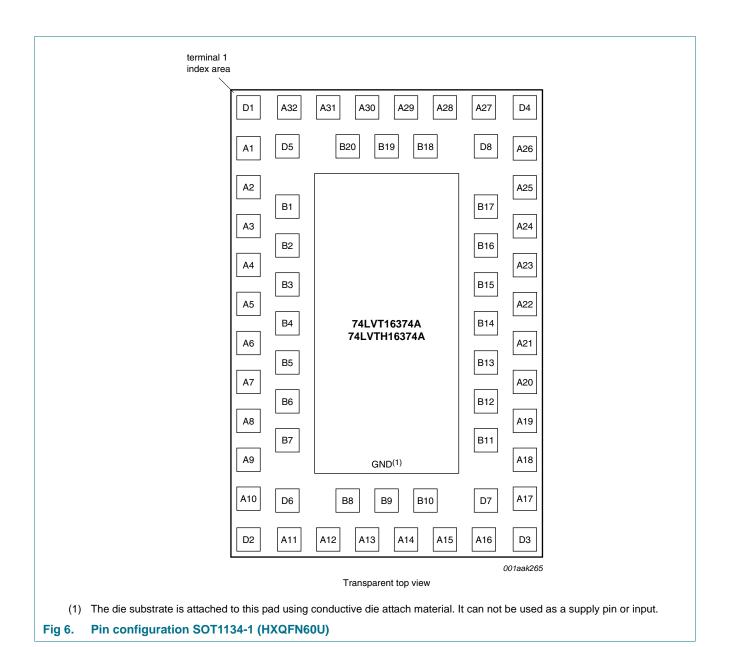




5. Pinning information

5.1 Pinning





5.2 Pin description

Table 2. Pin description

Symbol	Pin			Description
	SOT370-1 and SOT362-1	SOT702-1	SOT1134-1	
10E, 20E	1, 24	A1, K1	A30, A13	output enable input (active LOW)
1CP, 2CP	48, 25	A6, K6	A29, A14	clock input
1Q0 to 1Q7	2, 3, 5, 6, 8, 9, 11, 12	B2, B1, C2, C1, D2, D1, E2, E1	B20, A31, D5, D1, A2, B2, B3, A5	data output
2Q0 to 2Q7	13, 14, 16, 17, 19, 20, 22, 23	F1, F2, G1, G2, H1, H2, J1, J2	A6, B5, B6, A9, D2, D6, A12, B8	data output
GND	4, 10, 15, 21, 28, 34, 39, 45	B3, D3, G3, J3, J4, G4, D4, B4	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V _{CC}	7, 18, 31, 42	C3, H3, H4, C4	A1, A10, A17, A26	supply voltage
1D0 to 1D7	47, 46, 44, 43, 41, 40, 38, 37	B5, B6, C5, C6, D5, D6, E5, E6	B18, A28, D8, D4, A25, B16, B15, A22	data input
2D0 to 2D7	36, 35, 33, 32, 30, 29, 27, 26	F6, F5, G6, G5, H6, H5, J6, J5	A21, B13, B12, A18, D3, D7, A15, B10	data input
n.c.	-	A2, A3, A4, A5, K2, K3, K4, K5	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

6. Functional description

Table 3. Function table[1]

Operating mode	Input			Internal register	Output
	nOE	nCP	nDn		nQ0 to nQ7
Load and read register	L	\uparrow	I	L	L
	L	↑	h	Н	Н
Hold	L	NC	X	NC	NC
Disable outputs	Н	NC	X	NC	Z
	Н	↑	nDn	nDn	Z

^[1] H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the HIGH-to-LOW clock transition;

I = LOW voltage level one set-up time prior to the HIGH-to-LOW clock transition;

NC = no change;

X = don't care;

Z = high-impedance OFF-state;

 \uparrow = LOW-to-HIGH clock transition.

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L = LOW voltage level;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		5 7 7 5		10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
V_{I}	input voltage		[<u>1</u>] -0.5	+7.0	V
V _O	output voltage	output in OFF-state or HIGH-state	[1] -0.5	+7.0	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
I _O	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		[2] _	150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}$			
		(T)SSOP48 package	[3] _	500	mW
		VFBGA56 and HXQFN60U package	<u>[4]</u> -	1000	mW

^[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V_{IH}	HIGH-level input voltage		2.0	-	-	V
V_{IL}	LOW-level input voltage		-	-	8.0	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current	none	-	-	32	mA
		current duty cycle \leq 50 %; $f_i \geq$ 1 kHz	-	-	64	mA
T _{amb}	ambient temperature	in free-air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

^[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

^[3] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

^[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V _{IK}	input clamping voltage	$V_{CC} = 2.7 \text{ V}; I_{IK} = -18 \text{ mA}$	-1.2	-0.85	-	V
V _{OH}	HIGH-level output voltage	I_{OH} = -100 μ A; V_{CC} = 2.7 V to 3.6 V	$V_{CC}-0.2$	V_{CC}	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
V _{OL}	LOW-level output voltage	V _{CC} = 2.7 V				
		I _{OL} = 100 μA	-	0.07	0.2	V
		I _{OL} = 24 mA	-	0.3	0.5	V
		V _{CC} = 3.0 V				
		I _{OL} = 16 mA	-	0.25	0.4	V
		I _{OL} = 32 mA	-	0.3	0.5	V
		I _{OL} = 64 mA	-	0.4	0.55	V
V _{OL(pu)}	power-up LOW-level output voltage	V_{CC} = 3.6 V; I_{O} = 1 mA; V_{I} = V_{CC} or GND	[2] -	0.1	0.55	V
l _l	input leakage current	control pins				
		$V_{CC} = 3.6 \text{ V}; V_I = V_{CC} \text{ or GND}$	-	0.1	±1	μΑ
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; V_{I} = 5.5 \text{ V}$	-	0.4	10	μΑ
		input data pins	[3]			
		V _{CC} = 0 V or 3.6 V; V _I = 5.5 V	-	0.4	10	μΑ
		$V_{CC} = 3.6 \text{ V}; V_{I} = V_{CC}$	-	0.1	1	μΑ
		$V_{CC} = 3.6 \text{ V}; V_{I} = 0 \text{ V}$	-5	-0.4	-	μΑ
I _{OFF}	power-off leakage current	$V_{CC} = 0 \text{ V}$; V_{I} or $V_{O} = 0 \text{ V}$ to 4.5 V	-	0.1	±100	μΑ
I _{BHL}	bus hold LOW current	$V_{CC} = 3 \text{ V}; V_{I} = 0.8 \text{ V}$	75	135	-	μΑ
I _{BHH}	bus hold HIGH current	$V_{CC} = 3 \text{ V}; V_{I} = 2.0 \text{ V}$	-	-135	-75	μΑ
I _{BHLO}	bus hold LOW overdrive current	input data pins; V _I = 0 V to 3.6 V; V _{CC} = 3.6 V	[<u>4</u>] 500	-	-	μΑ
I _{BHHO}	bus hold HIGH overdrive current	input data pins; $V_I = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 3.6 \text{ V}$	[4] -	-	-500	μА
I _{LO}	output leakage current	output in HIGH-state when $V_O > V_{CC}$; $V_O = 5.5 \text{ V}; V_{CC} = 3.0 \text{ V}$	-	50	125	μА
I _{O(pu/pd)}	power-up/power-down output current	$V_{CC} \le \underline{1.2} \text{ V; } V_O = 0.5 \text{ V to } V_{CC}; V_I = \text{GND or } V_{CC}; n\overline{\text{OE}} = \text{don't care}$	<u>[5]</u> _	1	±100	μΑ
l _{OZ}	OFF-state output current	$V_{CC} = 3.6 \text{ V}; V_I = V_{IH} \text{ or } V_{IL}$				
		output HIGH: V _O = 3.0 V	-	0.5	5	μΑ
		output LOW: V _O = 0.5 V	-5	0.5	-	μΑ
I _{CC}	supply current	$V_{CC} = 3.6 \text{ V}$; $V_I = \text{GND or } V_{CC}$; $I_O = 0 \text{ A}$				
		outputs HIGH	-	0.07	0.12	mA
		outputs LOW	-	4.0	6.0	mA
		outputs disabled	[6] _	0.07	0.12	mA

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Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 3.0 V to 3.6 V; one input at V_{CC} – 0.6 V, other inputs at V_{CC} or GND	<u>[7]</u> -	0.1	0.2	mA
C _I	input capacitance	input pins; $V_1 = 0 \text{ V or } 3.0 \text{ V}$	-	3	-	pF
C _O	output capacitance	output pins nQn; outputs disabled; $V_O = 0 V$ or V_{CC}	-	9	-	pF

- [1] Typical values are measured at V_{CC} = 3.3 V and at T_{amb} = 25 °C.
- [2] For valid test results, data must not be loaded into the flips-flops (or latches) after applying power.
- [3] Unused pins at V_{CC} or GND.
- [4] This is the bus hold overdrive current required to force the input to the opposite logic state.
- This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.
- [6] I_{CC} is measured with outputs pulled to V_{CC} or GND.
- [7] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 10</u>.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
$T_{amb} = -40$	°C to +85 °C					
f_{max}	maximum frequency	nCP; V_{CC} = 3.3 V \pm 0.3 V; see Figure 7	150	-	-	MHz
t _{PLH}	LOW to HIGH	nCP to nQn; see Figure 7				
	propagation delay	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.9	5.0	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	5.6	ns
t_{PHL}	HIGH to LOW	nCP to nQn; see Figure 7				
	propagation delay	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	3.0	5.0	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	5.6	ns
t _{PZH}	OFF-state to HIGH propagation delay	nOE to nQn; see Figure 8				
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	3.2	4.8	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	6.0	ns
t _{PZL}	OFF-state to LOW	nOE to nQn; see Figure 8				
	propagation delay	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	3.0	4.6	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	5.2	ns
t _{PHZ}	HIGH to OFF-state	nOE to nQn; see Figure 8				
	propagation delay	V_{CC} = 3.3 V \pm 0.3 V	1.5	3.9	5.4	ns
		V _{CC} = 2.7 V	-	-	6.0	ns
t _{PLZ}	LOW to OFF-state	nOE to nQn; see Figure 8				
	propagation delay	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	3.4	4.6	ns
		V _{CC} = 2.7 V	-	-	5.0	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Parameter	Conditions	Min	Typ[1]	Max	Unit
set-up time	nDn to nCP; HIGH or LOW; see Figure 9	<u>[2]</u>			
	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.0	0.7	-	ns
	V _{CC} = 2.7 V	2.0	-	-	ns
hold time	nDn to nCP; HIGH or LOW; see Figure 9	[3]			
	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.8	0	-	ns
	V _{CC} = 2.7 V	0.1	-	-	ns
pulse width	nCP HIGH; see Figure 7	<u>[4]</u>			
	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	0.6	-	ns
	V _{CC} = 2.7 V	1.5	-	-	ns
	nCP LOW; see Figure 7				
	V_{CC} = 3.3 V \pm 0.3 V	3.0	1.6	-	ns
	$V_{CC} = 2.7 \text{ V}$	3.0	-	-	ns
	set-up time	set-up time $ \begin{array}{c} \text{nDn to nCP; HIGH or LOW; see } \underline{\text{Figure 9}} \\ V_{\text{CC}} = 3.3 \text{ V} \pm 0.3 \text{ V} \\ V_{\text{CC}} = 2.7 \text{ V} \\ \\ \text{hold time} \\ \hline \begin{array}{c} \text{nDn to nCP; HIGH or LOW; see } \underline{\text{Figure 9}} \\ V_{\text{CC}} = 3.3 \text{ V} \pm 0.3 \text{ V} \\ V_{\text{CC}} = 2.7 \text{ V} \\ \\ \text{pulse width} \\ \hline \begin{array}{c} \text{nCP HIGH; see } \underline{\text{Figure 7}} \\ V_{\text{CC}} = 3.3 \text{ V} \pm 0.3 \text{ V} \\ V_{\text{CC}} = 2.7 \text{ V} \\ \\ \text{nCP LOW; see } \underline{\text{Figure 7}} \\ V_{\text{CC}} = 3.3 \text{ V} \pm 0.3 \text{ V} \\ \\ \end{array} $	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Waveforms

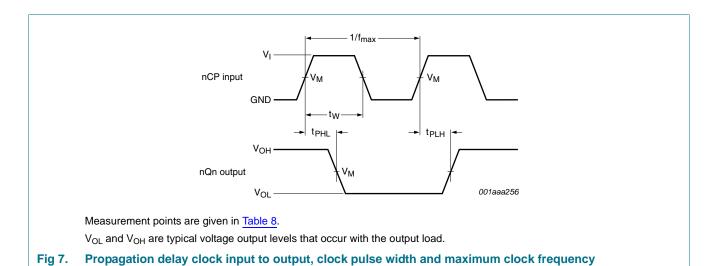


Table 8. Measurement points

Input	Output		
V_{M}	V _M	V _X	V _Y
1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V

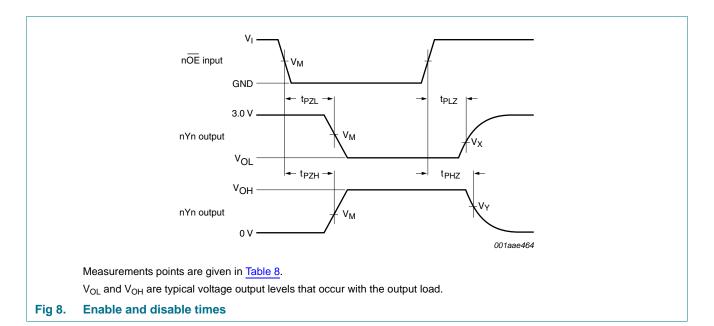
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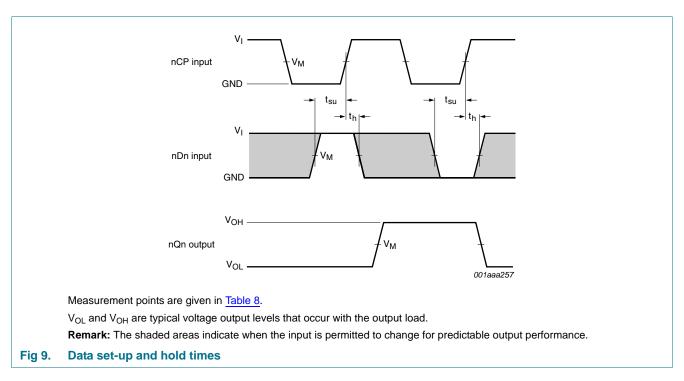
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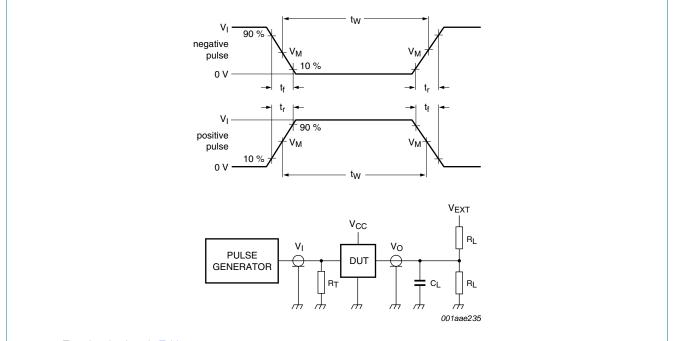
^[2] t_{su} is the same as $t_{su(H)}$ and $t_{su(L)}$.

 $^{[3] \}quad t_h \text{ is the same as } t_{h(H)} \text{ and } t_{h(L)}.$

^[4] t_W is the same as $t_{W(H)}$ and $t_{W(L)}$.







Test data is given in Table 9.

Definitions test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = Test voltage for switching times.

Fig 10. Test circuit for measuring switching times

Table 9. Test data

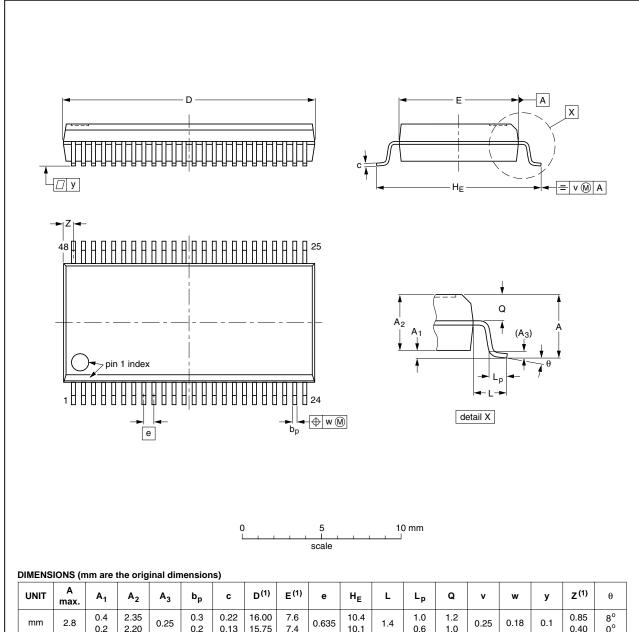
Input				Load		V _{EXT}			
V_{I}	f _i t _W		t_r, t_f C_L R_L			t _{PHZ} , t _{PZH}	t_{PLZ}, t_{PZL}	t _{PLH} , t _{PHL}	
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	50 pF	500Ω	GND	6 V	open	

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12. Package outline

SSOP48: plastic shrink small outline package; 48 leads; body width 7.5 mm

SOT370-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2.8	0.4 0.2	2.35 2.20	0.25	0.3 0.2	0.22 0.13	16.00 15.75	7.6 7.4	0.635	10.4 10.1	1.4	1.0 0.6	1.2 1.0	0.25	0.18	0.1	0.85 0.40	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT370-1		MO-118				99-12-27 03-02-19	

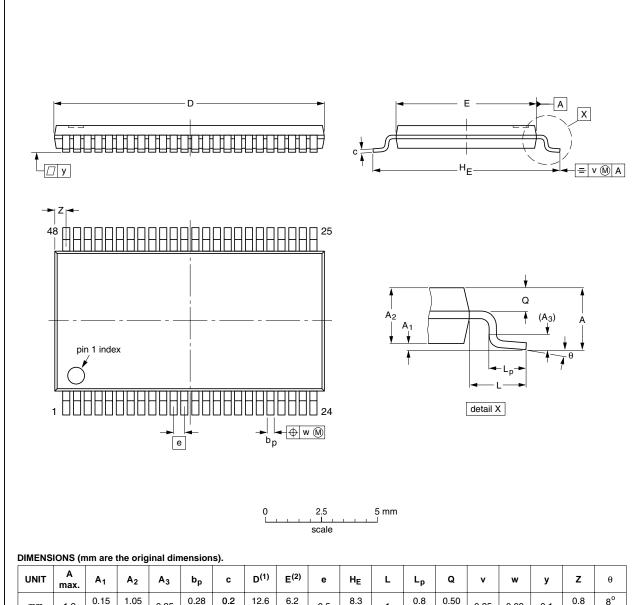
Fig 11. Package outline SOT370-1 (SSOP48)

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TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm

SOT362-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	12.6 12.4	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.8 0.4	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT362-1		MO-153				99-12-27 03-02-19

Fig 12. Package outline SOT362-1 (TSSOP48)

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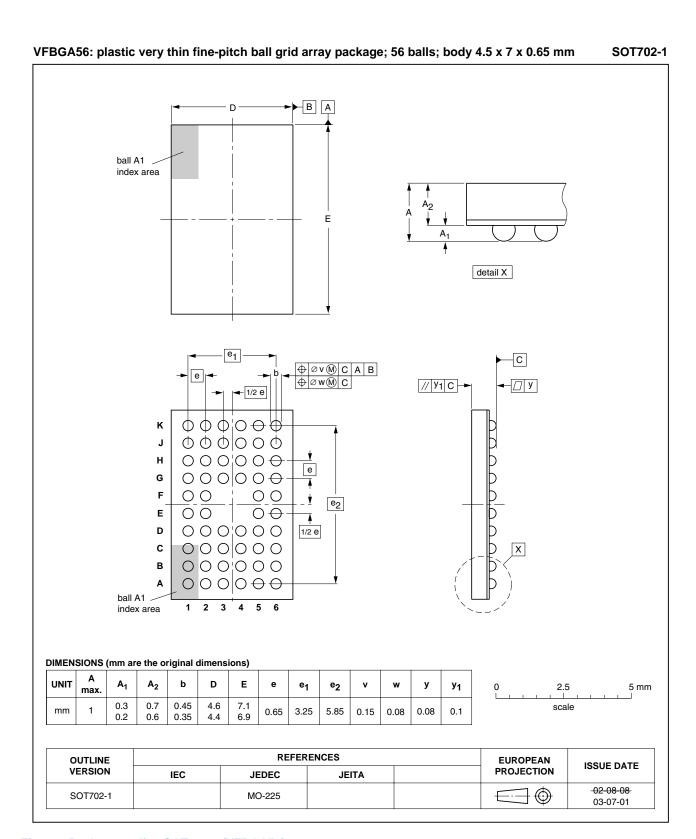


Fig 13. Package outline SOT702-1 (VFBGA56)

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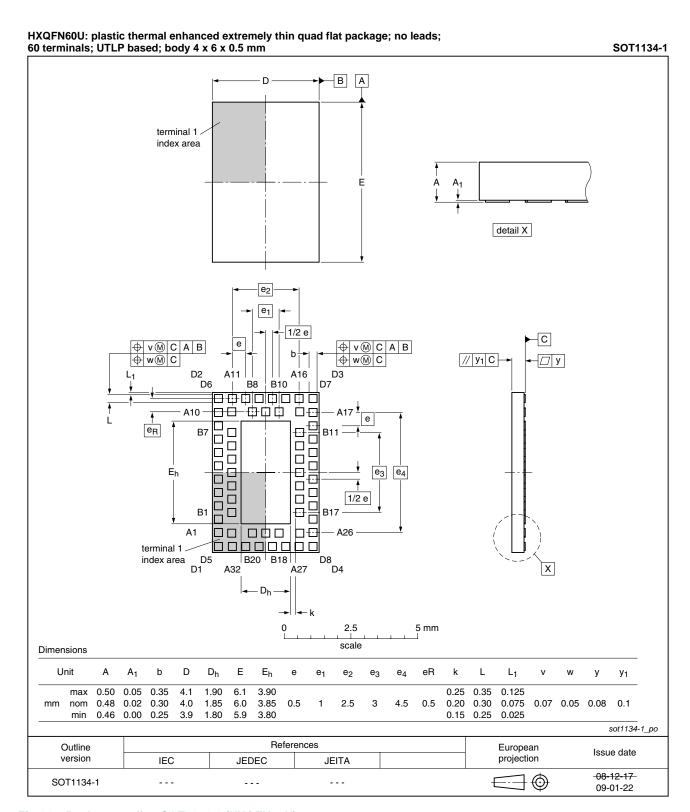


Fig 14. Package outline SOT1134-1 (HXQFN60U)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVT_LVTH16374A_7	20100322	Product data sheet	-	74LVT_LVTH16374A_6
Modifications:	 74LVTH163 package. 	74ABQ changed from HUC	QFN60U (SOT1025-1) to	HXQFN60U (SOT1134-1)
74LVT_LVTH16374A_6	20100118	product data sheet	-	74LVT16374A_5
Modifications:	guidelines o	of this data sheet has been of NXP Semiconductors.		·
	 Legal texts I 	have been adapted to the r	new company name whe	re appropriate.
	 Added type (HUQFN60I 	numbers 74LVTH16374AD J)	DGG (TSSOP48) and 74	LVTH16374ABQ
74LVT16374A_5	20040916	product data sheet	-	74LVT16374A_4
74LVT16374A_4	20021101	product specification	-	74LVT16374A_3
74LVT16374A_3	19991018	product specification	-	74LVT16374A_2
74LVT16374A_2	19980219	product specification	-	-

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15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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3.3 V 16-bit edge-triggered D-type flip-flop; 3-state

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